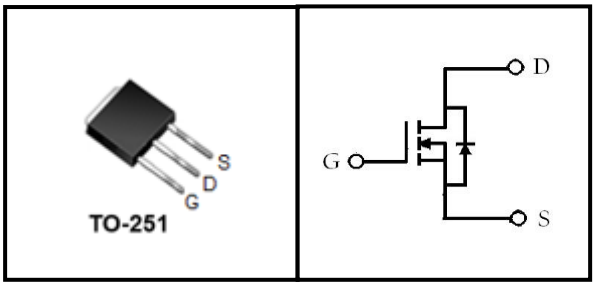
200V N-Channel Trench MOSFET

FEATURES

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology



APPLICATIONS

- Power switching application
- Uninterruptible Power Supply
- Hard switched and high frequency circuits

RoHS

Device Marking and Package Information

Device	Package	Marking
CTU20N700	TO-251	CTU20N700

Absolute Maximum Ratings at T_j= 25ºC unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	200	V
Continuous Drain Current T_C = 25ºC (note1)	I_D	2.8	A
Continuous Drain Current T_C = 100ºC (note1)		1.5	A
Drain Current-Continuous@ Current-Pulsed (note2)	I_{DM}	8	A
Gate-Source Voltage (VDS=0V)	V_{GSS}	±20	V
Single Pulse Avalanche Energy (note3)	E_{AS}	8	mJ
Maximum Power Dissipation(Tc=25℃) (note4)	P_D	42	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175	ºC

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.6	ºC/W
Thermal Resistance, Junction-to-Ambient (note1)	$R_{\theta JA}$	62	

Electrical Characteristics T_j= 25ºC unless otherwise specified						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	200	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 200V, V_{GS} = 0V, T_J = 25ºC	--	--	1	uA
		V_{DS} = 200V, V_{GS} = 0V, T_J = 55ºC	--	--	5	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	2.0	3.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 1A	--	560	700	mΩ
		V_{GS} = 4.5V, I_D = 1A	--	650	900	Ω
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz	--	900	--	pF
Output Capacitance	C_{oss}		--	130	--	
Reverse Transfer Capacitance	C_{rss}		--	4.6	--	
Total Gate Charge	Q_g	V_{DS} = 160V, I_D = 1A, V_{GS} = 10V	--	15	--	nC
Gate-Source Charge	Q_{gs}		--	3	--	
Gate-Drain Charge	Q_{gd}		--	5.2	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 100V, I_D = 1A, R_G = 3Ω, V_{GS}=10V,	--	22	--	ns
Turn-on Rise Time	t_r		--	34	--	
Turn-off Delay Time	$t_{d(off)}$		--	45	--	
Turn-off Fall Time	t_f		--	11	--	
Body Diode Characteristics						
Continuous Body Diode Current	I_S		--	--	2.8	A
Pulsed Diode Forward Current	I_{SM}		--	--	8	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 1A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	t_{rr}	I_F = 1A di_F/dt = 100A/μs TJ=25℃	--	85	--	ns
Reverse Recovery Charge	Q_{rr}		--	257	--	nC

Notes

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width≦300us , duty cycle≦2%
3.The EAS data shows Max. rating . The test condition is VDD =25V,VGS =10V,L=0.1mH
4.The power dissipation is limited by 175℃ junction temperature
5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics T_J = 25ºC, unless otherwise noted

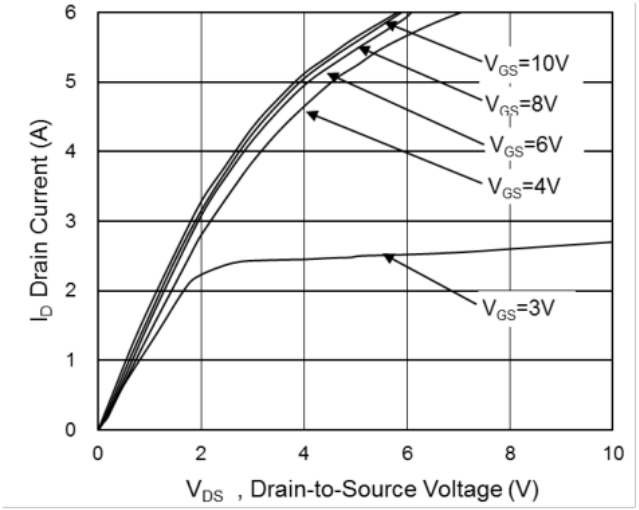


Fig.1 Typical Output Characteristics

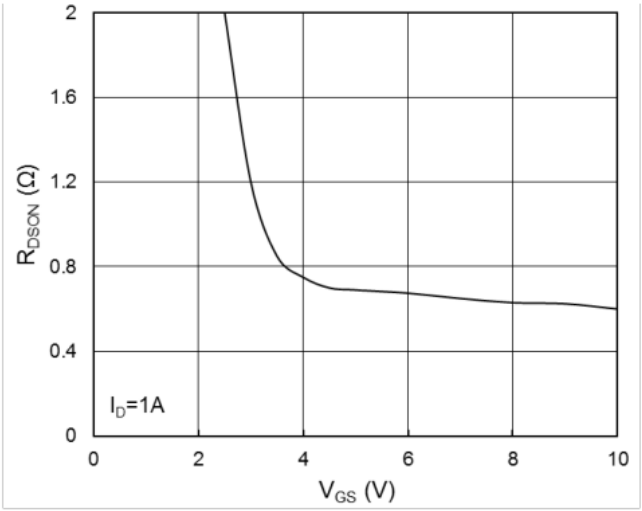


Fig.2 On-Resistance vs. G-S Voltage

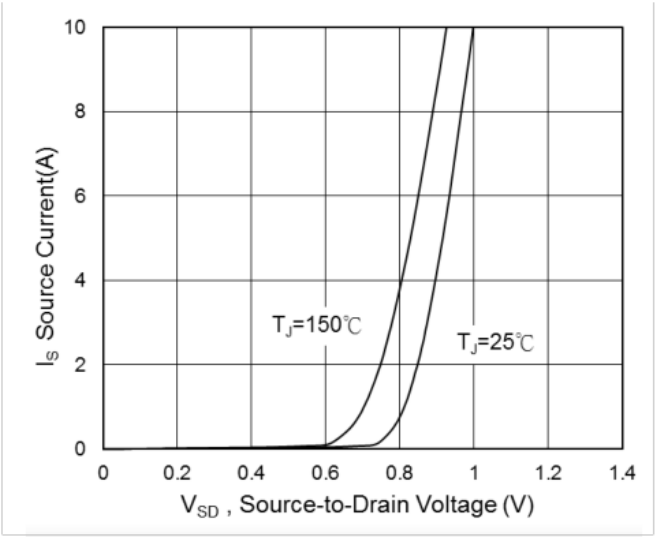


Fig.3 Forward Characteristics of ReverseDiode

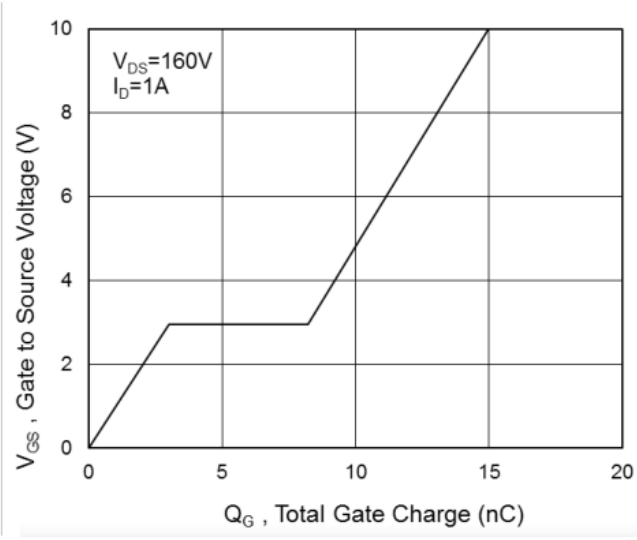


Fig.4 Gate-Charge Characteristics

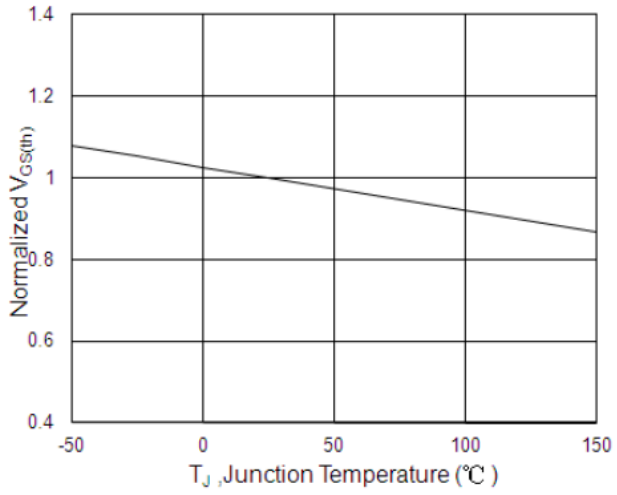


Fig.5 Normalized VGS(th)vs. TJ

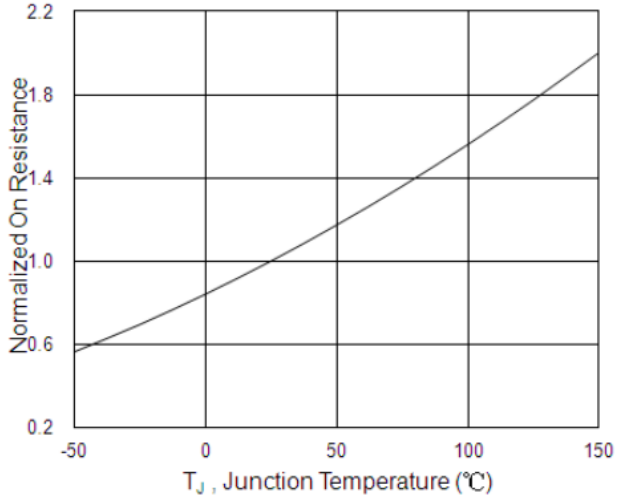


Fig.6 Normalized RDSONvs. TJ

Typical Characteristics T_J = 25ºC, unless otherwise noted

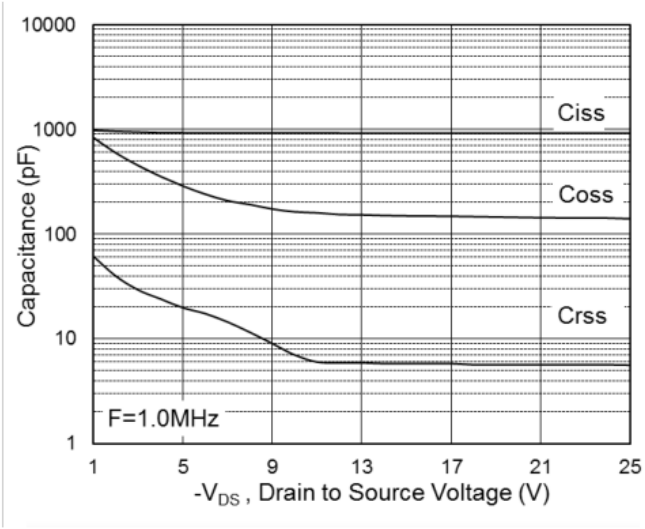


Fig.7 Capacitance

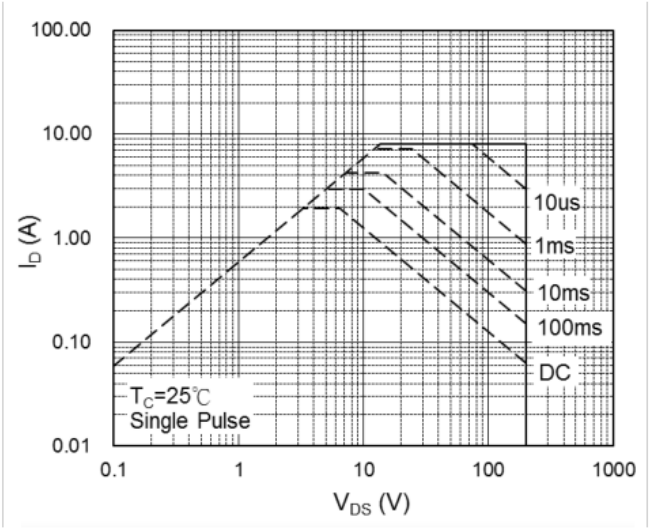


Fig.8 Safe Operating Area

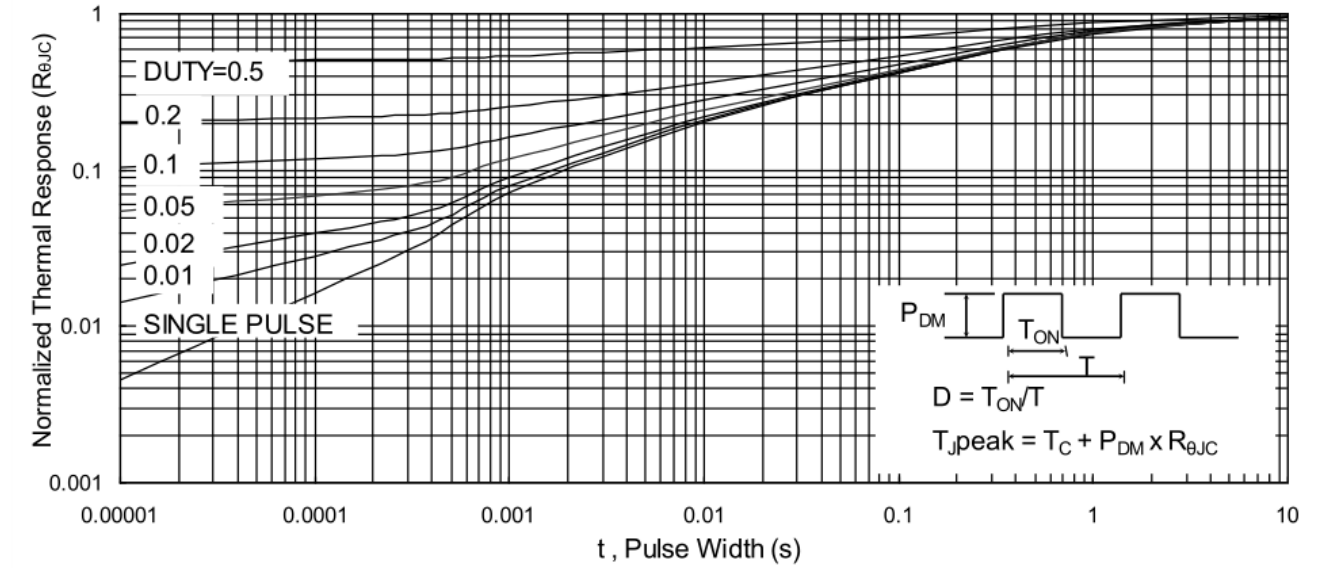


Fig.9 Normalized Maximum Transient Thermal Impedance

Figure A：Gate Charge Test Circuit and Waveform

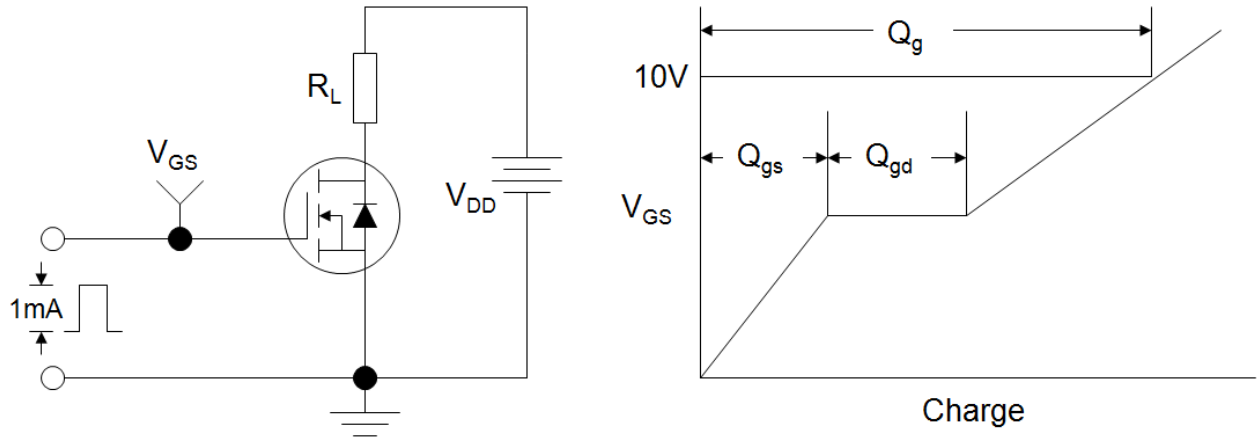


Figure B：Resistive Switching Test Circuit and Waveform

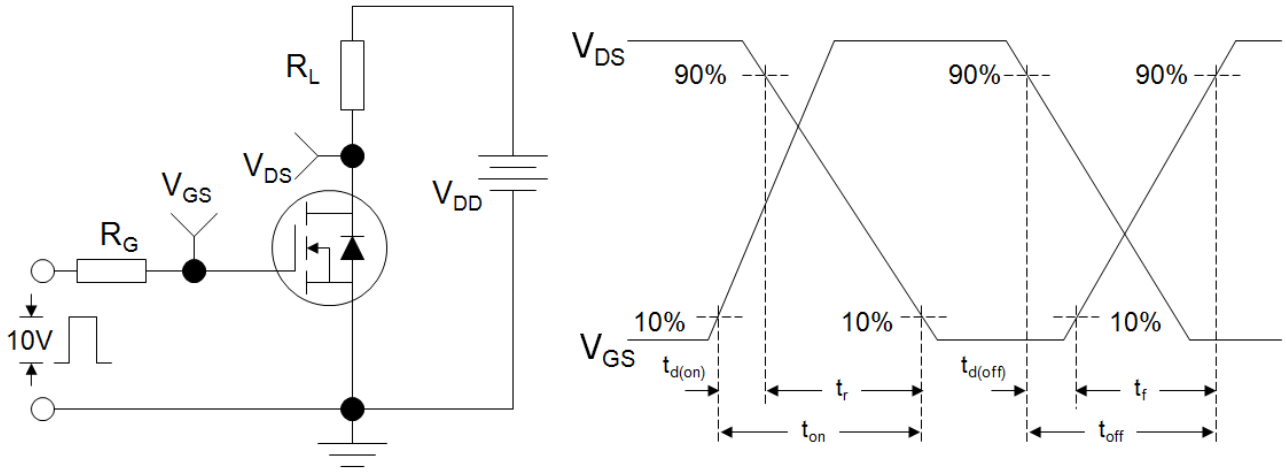
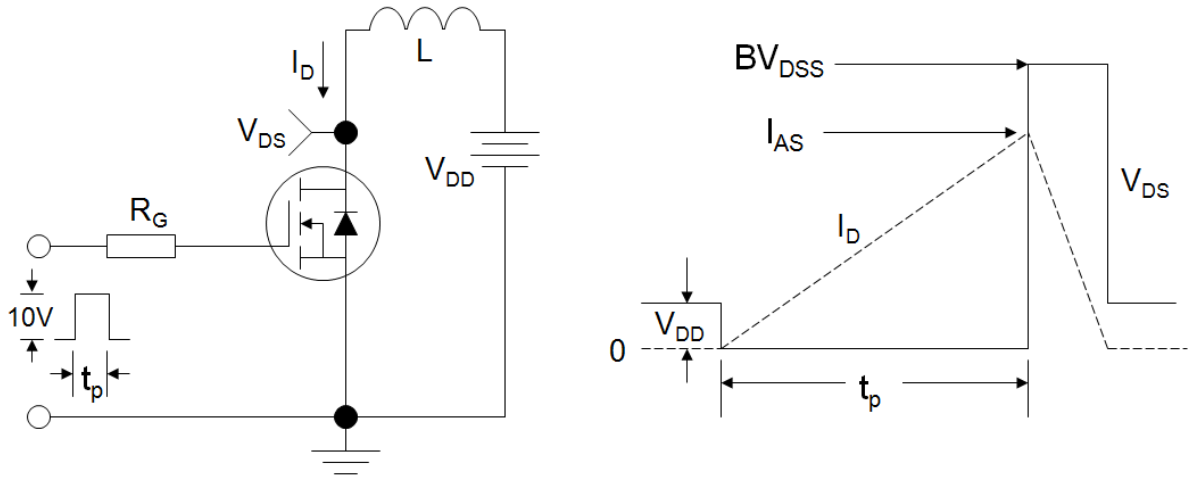


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



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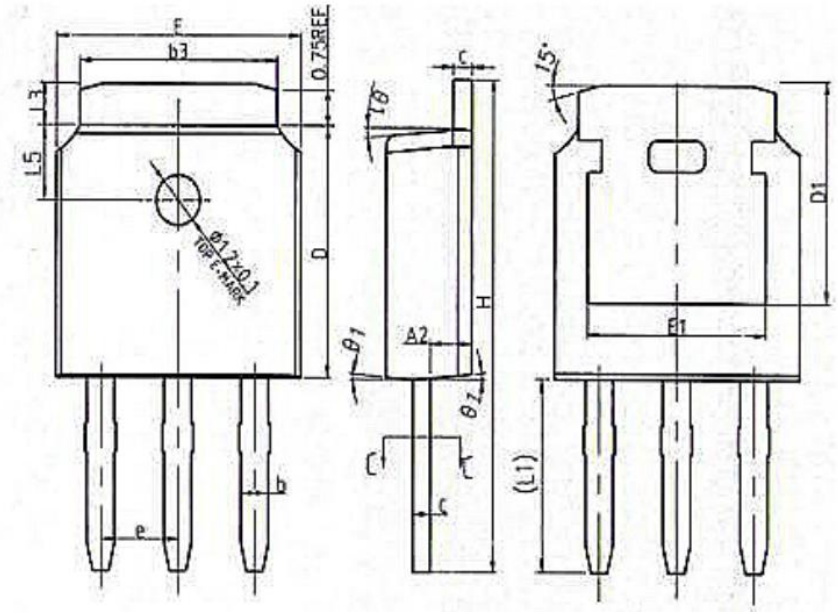

Symbol	mm		
	Min	Typ	Max
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.72	0.78	0.85
b1	0.71	0.76	0.81
b3	5.23	5.33	5.46
c	0.47	0.53	0.58
C1	0.46	0.51	0.56
D	6.00	6.10	6.20
D1		5.30REF	
E	6.50	6.60	6.70
E1	4.70	4.83	4.92
e		2.286BSC	
H	10	11.2	11.40
L1	4.00	4.10	4.20
L3	0.90	1.02	1.25
L5	1.70	1.80	1.90
θ1	5°	7°	9°
θ2	5°	7°	9°
K		0.40REF	

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